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Appn. Number: 10/081,963
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Applicant: GEIST, Jon
Appn. Title: Method for TMAH etching of CMOS integrated circuits
Examiner: DuyVun Deo

Mailed: 2004 SEP 20
Olney MD 20832

AMENDEMNT A

Commissioner of Patents and Trademarks
Washington DC 20231

Sir:

In response to the Office Letter mailed 2004 JULY 01, please amend the above application as follows:

CLAIMS:

Cancel all claims of record and substitute new Claims 10-17 as follows:

10. A method for preparing an etchant comprising a solution of tetramethylammonium hydroxide and water, wherein
 - A liquid source of silicate ions is mixed with said solution, and
 - An oxidizer is added to said etchant at a time later than 10 minutes following immersion of a sample comprised of silicon in said etchant.
11. The method of Claim 10 wherein said oxidizer is ammonium peroxydisulfate.
12. The method of Claim 10 wherein said oxidizer is obtained from a liquid source of oxidizer.
13. The method of Claim 12 wherein said liquid source of oxidizer is a solution of ammonium peroxydisulfate in water.
14. The method of Claim 10 wherein a quantity of tetramethylammonium hydroxide is added to said etchant at a time later than ten minutes following immersion of said sample in said etchant.
15. The method of Claim 14 wherein said quantity of tetramethylammonium hydroxide is added to said etchant following the addition of said oxidizer and said quantity of tetramethylammonium hydroxide is substantially the same as the quantity required to maintain the pH of